

Si-NPN - Photo transistor - type FT-30

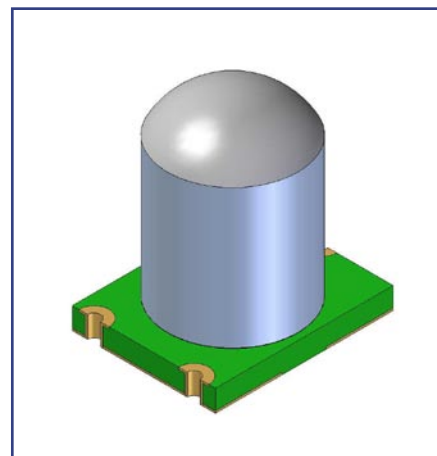


CHARACTERISTICS

- ▶ Integrated, coordinated high-efficiency optics
- ▶ No additional lenses required
- ▶ Extremely small reception and squint angles
- ▶ 3mm model, metal housing

APPLICATION

- ▶ For optical sensors



▶ **ELECTRONIC VALUES**

Parameter	Test conditions	typ. value	Unit
Dark current I_{ceo}	$V_{ce}=20V$; $H=0mW/cm^2$	< 100	nA
Collector-emitter saturation voltage V_{cesat}	$I_c=2mA$; $I_b= 100\mu A$	<0,3	V
Collector-emitter -breakout (U_{ceo})	$I_c=100\mu A$; $I_b=0$	>60	V
Current gain(H_{fe})	650nm 875nm 940nm	95 148 95	A/W
Emitter- Collector breakout (V_{eco})	$I_e=100\mu A$; $I_b=0$	>5	V
Supply voltage		+0.....+30	V

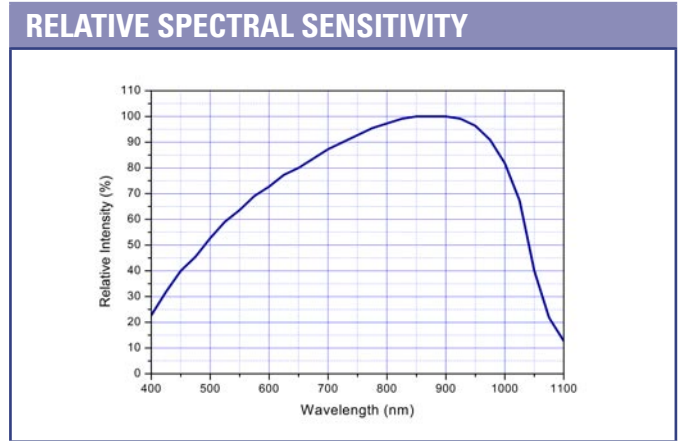
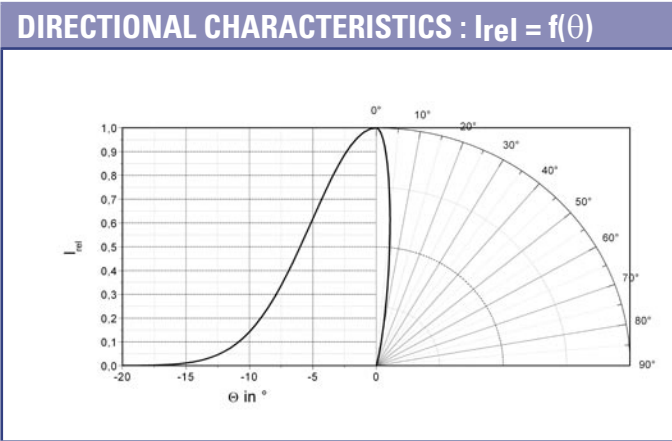
▶ **TYPICAL VALUES**

Parameter	Test conditions	typ. value	Unit
Spectral range of sensitivity		400-1000	nm
Rise and fall time of the photocurrent t_{r} t_{f}	10%-90% ; $I_c=1mA$, $V_{ce}=5V$; $R_l=1k\Omega$	15 15	μsec μsec
Dimensions of radiant sensitive area (A)		0,11	mm ²
Half power angle (θ)		6	deg

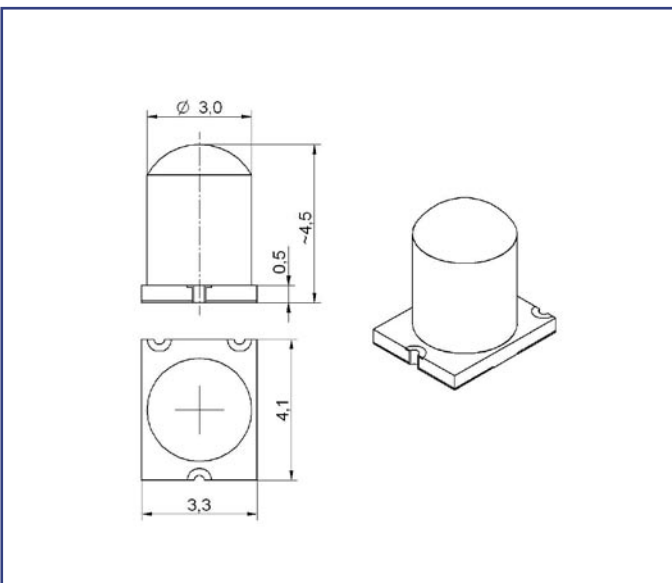


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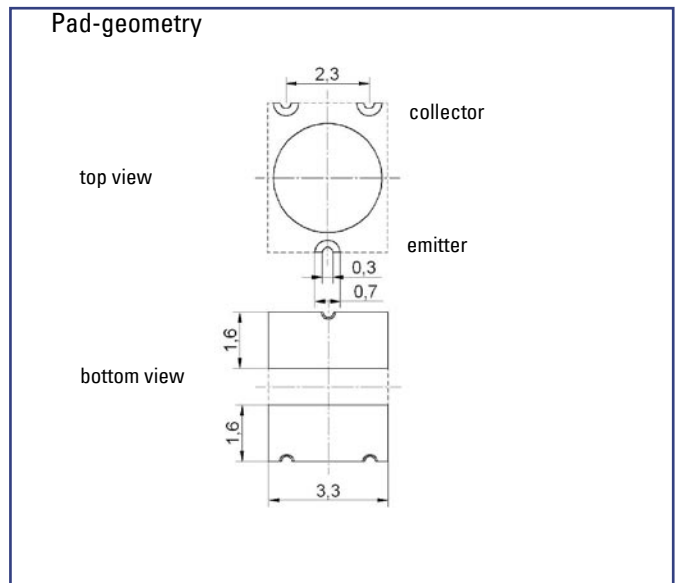
▶ **GRAPHS**



▶ **DIMENSIONS**



▶ **CONNECTOR PIN-ASSIGNMENT**



PART DESIGNATION	OE-FT-30-VA1-SL21-2-0115
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